BLF8G24LS-150V; Power LDMOS transistor Rev. 4 — 1 September 2015

AMPLEON

Product data sheet

Product profile

1.1 General description

150 W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 2300 MHz to 2400 MHz.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25$ °C in a common source class-AB production test circuit.

Test signal	f	I _{Dq}	V _{DS}	P _{L(AV)}	Gp	η_D	ACPR _{5M}
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2300 to 2400	1300	28	45	19	33	-30 <u>[1]</u>

^{[1] 3}GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz. Channel bandwidth is 3.84 MHz.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth (70 MHz typical)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Design optimized for gull-wing
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

RF power amplifiers for base stations and multi carrier applications in the 2300 MHz to 2400 MHz frequency range

2. Pinning information

Table 2. Pinning

	Z. 1 mming		
Pin	Description	Simplified outline	Graphic symbol
BLF8	G24LS-150V (SOT1244B)		
1	drain	4 1 5	4
2	gate	4 1 5	6,7 -1 -4,5
3	source [1]		2
4	decoupling lead	3	3
5	decoupling lead		aaa-003619
6	n.c.		
7	n.c.	6 2 7	
BLF8	G24LS-150GV (SOT1244C)	·	.
1	drain	4 1 5	4
2	gate	4 1 5	6,7 → 1 → 4,5
3	source [1]		2
4	decoupling lead		3
5	decoupling lead	6 2 7	aaa-003619
6	n.c.	3	
7	n.c.		

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	e number Package			
	Name	Description	Version	
BLF8G24LS-150V	-	earless flanged ceramic package; 6 leads	SOT1244B	
BLF8G24LS-150GV	-	earless flanged ceramic package; 6 leads	SOT1244C	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbo	Parameter Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	T _{case} = 80 °C; P _L = 45 W	0.30	K/W

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.16 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 216 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 1300 mA	1.6	2	2.4	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	4.5	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	-	40	-	А
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	450	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 10.8 A	-	16	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 7.56 \text{ A}$	-	0.06	-	Ω

Table 7. RF characteristics

Test signal: 2-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on the CCDF, carrier spacing 5 MHz; f_1 = 2302.5 MHz; f_2 = 2307.5 MHz; f_3 = 2392.5 MHz; f_4 = 2397.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 1300 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _{L(AV)} = 45 W	17.5	19	-	dB
RLin	input return loss	P _{L(AV)} = 45 W	-	-10	-7	dB
η_{D}	drain efficiency	P _{L(AV)} = 45 W	29	33	-	%
ACPR _{5M}	adjacent channel power ratio (5 MHz)	P _{L(AV)} = 45 W	-	-30	-27	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLF8G24LS-150V and BLF8G24LS-150GV are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; $I_{Dq} = 1300 \text{ mA}$; $P_L = 150 \text{ W}$ (CW); f = 2300 MHz.

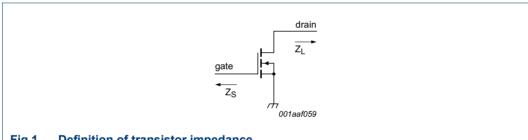
7.2 Impedance information

Table 8. **Typical impedance**

Measured load-pull data; $I_{Dq} = 1300 \text{ mA}$; $V_{DS} = 28 \text{ V}$.

f	Z _S [1]	Z _L [1]
(MHz)	(Ω)	(Ω)
BLF8G24LS-150V		
2300	1.25 – j4.11	2.95 – j1.20
2400	2.34 – j5.50	2.88 – j1.31
2500	5.65 – j6.35	2.80 – j1.35
BLF8G24LS-150GV		
2300	1.29 – j5.78	3.13 – j3.26
2400	2.15 – j7.09	2.78 – j3.44
2500	6.61 – j7.57	2.98 – j3.66

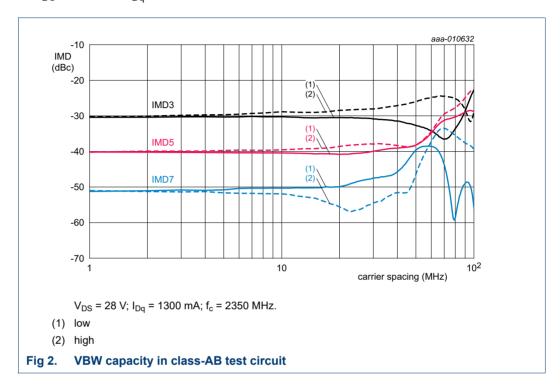
[1] Z_S and Z_L defined in Figure 1.



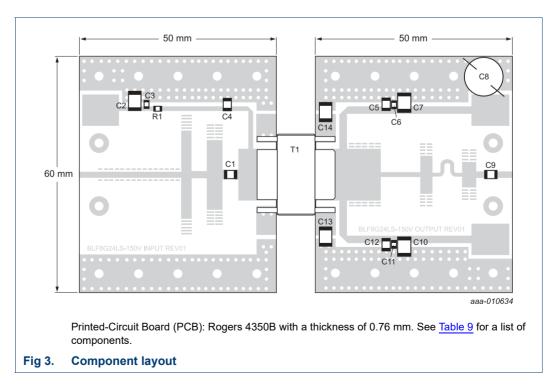
Definition of transistor impedance Fig 1.

7.3 VBW in a class-AB operation

The BLF8G24LS-150V shows 70 MHz (typical) video bandwidth (IMD third-order intermodulation inflection point) in a class-AB test circuit in the 2.3 GHz to 2.4 GHz band at V_{DS} = 28 V and I_{Dg} = 1.3 A.



7.4 Test circuit



BLF8G24LS-150V_8G24LS-150GV#4

Table 9. List of components

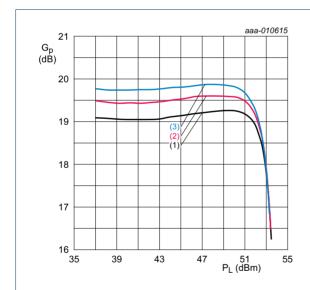
See Figure 3 for component layout.

Component	Description	Value		Remarks
C1	multilayer ceramic chip capacitor	1.2 pF	[1]	ATC 800B
C2	multilayer ceramic chip capacitor	1 μF	[2]	Murata
C3	multilayer ceramic chip capacitor	100 nF	[2]	Murata
C4, C5, C9, C12	multilayer ceramic chip capacitor	24 pF	[1]	ATC 800B
C6, C11	multilayer ceramic chip capacitor	220 nF	[2]	Murata
C7, C10, C13, C14	multilayer ceramic chip capacitor	4.7 μF, 50 V	[2]	Murata
C8	electrolytic capacitor	> 470 μF, 63 V		
R1	chip resistor	4.7 Ω, 1 % tolerance		SMD 0805
T1	transistor	-		Ampleon BLF8G24LS-150V

- [1] American Technical Ceramics type 800B or capacitor of same quality.
- [2] Murata or capacitor of same quality.

7.5 Graphical data

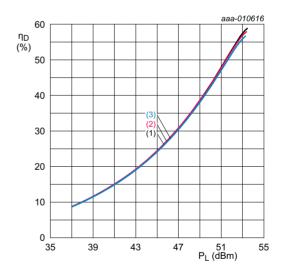
7.5.1 Pulsed CW



 V_{DS} = 28 V; I_{Dq} = 1300 mA; t_p = 100 μ s; δ = 10 %.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 4. Power gain as a function of output power; typical values

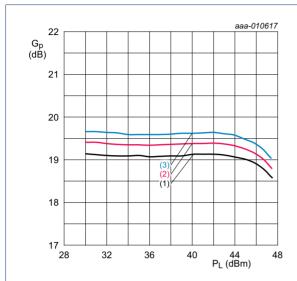


 V_{DS} = 28 V; I_{Dq} = 1300 mA; t_p = 100 μ s; δ = 10 %.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 5. Drain efficiency as a function of out power; typical values

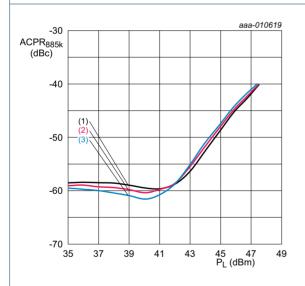
7.5.2 IS-95



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

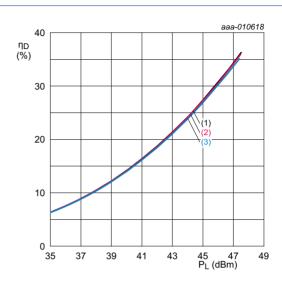
Fig 6. Power gain as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

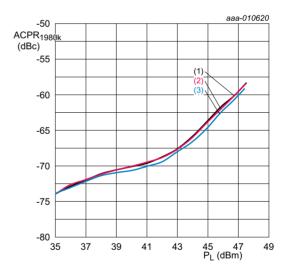
Fig 8. Adjacent channel power ratio (885 kHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 7. Drain efficiency as a function of output power; typical values

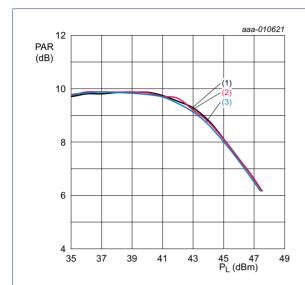


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 9. Adjacent channel power ratio (1980 kHz) as a function of output power; typical values

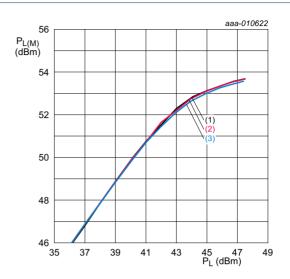
Power LDMOS transistor



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 10. Peak-to-average ratio as a function of output power; typical values

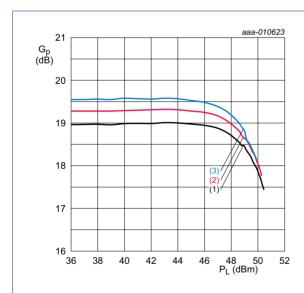


 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 11. Peak output power as a function of output power; typical values

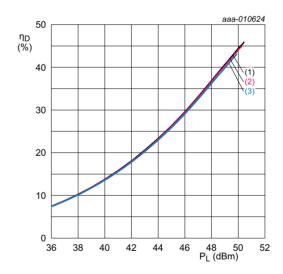
7.5.3 1-Carrier W-CDMA



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 12. Power gain as a function of output power; typical values

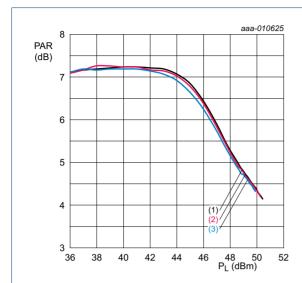


 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 13. Drain efficiency as a function of output power; typical values

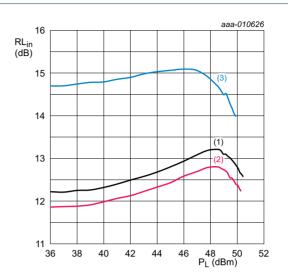
Power LDMOS transistor



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 14. Peak-to-average ratio as a function of output power; typical values

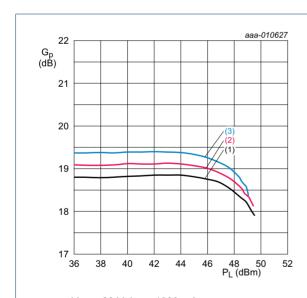


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 15. Input return loss as a function of output power; typical values

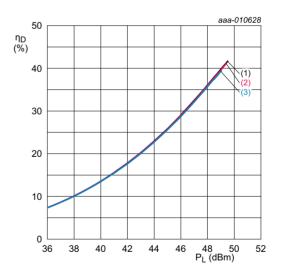
7.5.4 2-Carrier W-CDMA



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 16. Power gain as a function of output power; typical values

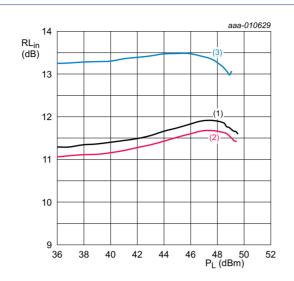


 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 17. Drain efficiency as a function of output power; typical values

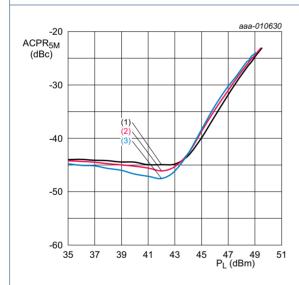
Power LDMOS transistor



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

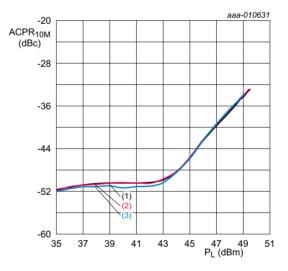
Fig 18. Input return loss as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 19. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 20. Adjacent channel power ratio (10 MHz) as a function of output power; typical values

8. Package outline

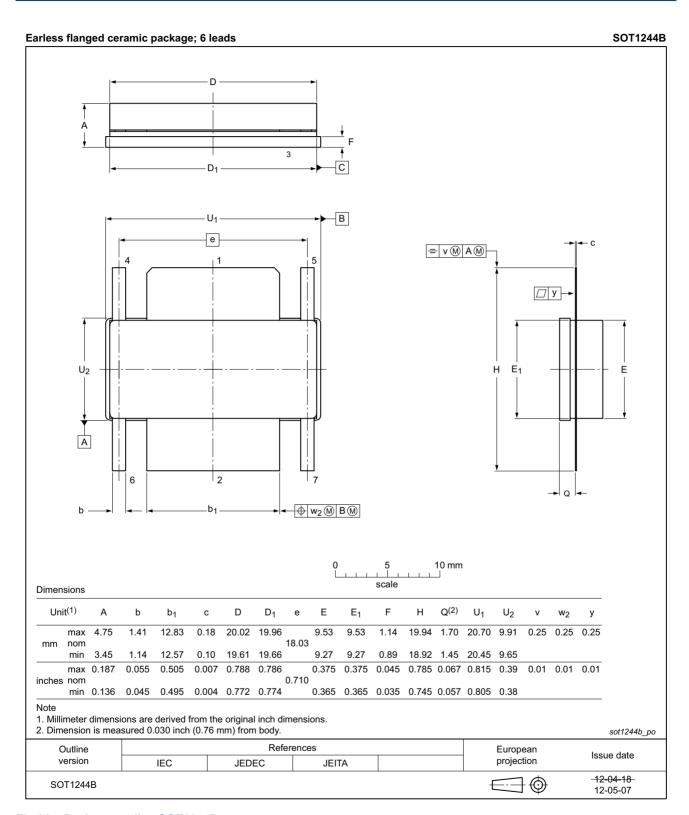


Fig 21. Package outline SOT1244B

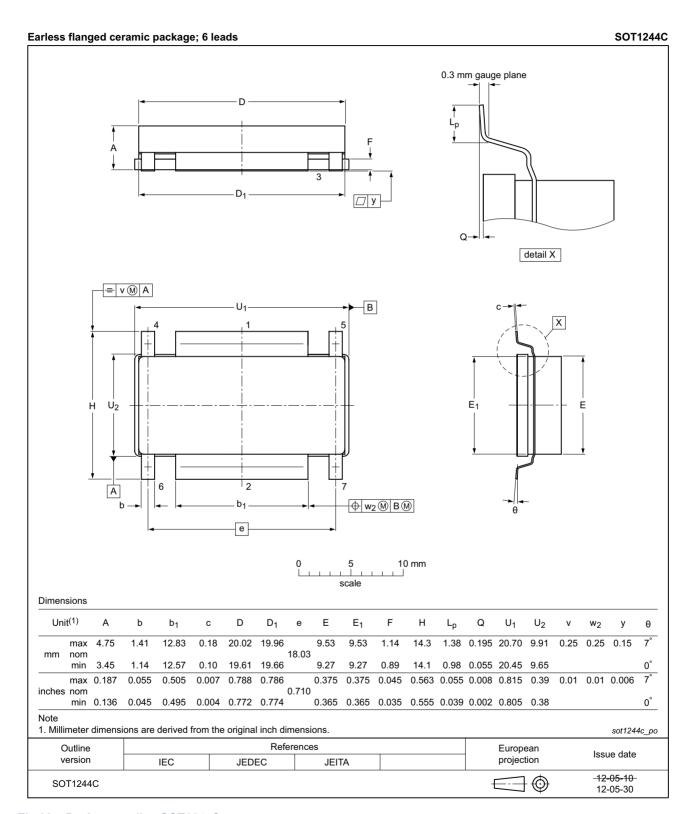


Fig 22. Package outline SOT1244C

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description	
3GPP	Brd Generation Partnership Project	
CCDF	Complementary Cumulative Distribution Function	
CW	Continuous Wave	
DPCH	Dedicated Physical CHannel	
ESD	ElectroStatic Discharge	
IS-95	Interim Standard 95	
LDMOS	Laterally Diffused Metal Oxide Semiconductor	
MTF	Median Time to Failure	
PAR	Peak-to-Average Ratio	
SMD	Surface Mounted Device	
VBW	Video BandWidth	
VSWR	Voltage Standing Wave Ratio	
W-CDMA	Wideband Code Division Multiple Access	

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF8G24LS-150V_8G24LS-150GV#4	20150901	Product data sheet		BLF8G24LS-150V_ 8G24LS-150GV v.3	
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. 				
BLF8G24LS-150V_8G24LS-150GV v.3	20140512	Product data sheet	-	BLF8G24LS-150V_ 8G24LS-150GV v.2	
BLF8G24LS-150V_8G24LS-150GV v.2	20140224	Objective data sheet	-	BLF8G24LS-150V_ 8G24LS-150GV v.1	
BLF8G24LS-150V_8G24LS-150GV v.1	20131104	Objective data sheet	-	-	

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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BLF8G24LS-150V 8G24LS-150GV#4

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Power LDMOS transistor

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BLF8G24LS-150(G)V

Power LDMOS transistor

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.